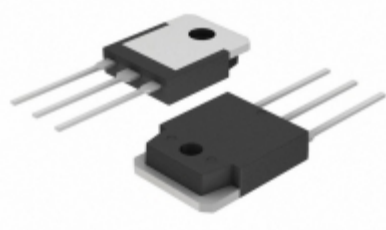



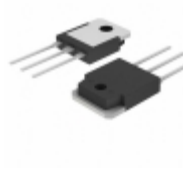


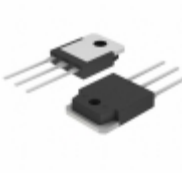
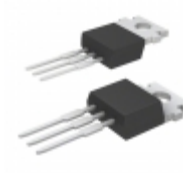

	GP2M011A090NG	
	Hersteller-Teilenummer:	GP2M011A090NG
	Hersteller / Marke:	Global Power Technologies Group
	Teil der Beschreibung:	MOSFET N-CH 900V 11A TO3PN
	Datenblätter:	 GP2M011A090NG.pdf
	RoHs Status:	Bleifrei / RoHS-konform
	Lagerzustand:	New original, 1700 pcs Stock Available.
	Liefern von:	Hong Kong
	Versandweg:	DHL/Fedex/TNT/UPS/EMS
Image may be representation. See specs for product details.		

Spezifikationen

Teilenummer	GP2M011A090NG
Hersteller	Global Power Technologies Group
Beschreibung	MOSFET N-CH 900V 11A TO3PN
Kategorie	Diskrete Halbleiterprodukte > Transistoren-FETs ,
Teilstatus	1700 pcs Stock
Serie	-
Technologie	MOSFET (Metal Oxide)
Betriebstemperatur	-55°C ~ 150°C (TJ)
Befestigungsart	Through Hole
Verpackung / Gehäuse	TO-3P-3, SC-65-3
Supplier Device-Gehäuse	TO-3PN
Verlustleistung (max)	416W (Tc)
Typ FET	N-Channel
FET-Merkmal	-
Drain-Source-Spannung (Vdss)	900V
Strom - Ununterbrochener Abfluss (Id) bei 25 ° C	11A (Tc)
Rds On (Max) @ Id, Vgs	900 mOhm @ 5.5A, 10V
VGS (th) (Max) @ Id	5V @ 250µA
Gate Charge (Qg) (Max) @ Vgs	84nC @ 10V
Eingabekapazität (Ciss) (Max) @ Vds	3240pF @ 25V
Verpackung	Tube

























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Sie können auch interessiert sein:

 <p>GP2M020A050F Global Power Technologies Group MOSFET N-CH 500V 18A TO220F</p>	 <p>GP2M010A060F Global Power Technologies Group MOSFET N-CH 600V 10A TO220F</p>	 <p>GP2M012A080NG Global Power Technologies Group MOSFET N-CH 800V 12A TO3PN</p>	 <p>GP2M010A065H Global Power Technologies Group MOSFET N-CH 650V 9.5A TO220</p>
 <p>GP2M013A050F Global Power Technologies Group MOSFET N-CH 500V 13A TO220F</p>	 <p>GP2M009A090NG Global Power Technologies Group MOSFET N-CH 900V 9A TO3PN</p>	 <p>GP2M012A060H Global Power Technologies Group MOSFET N-CH 600V 12A TO220</p>	 <p>GP2M010A065F Global Power Technologies Group MOSFET N-CH 650V 9.5A TO220F</p>

heiße Teile

Mehr

 GP2A25J0000F	 GP2A25J0000F	 GP2A25NJ	 GP2A28A1J00F	 GP2A28N1J00F
 GP2AP002A00F	 GP2AP002S00F	 GP2AP003A10F	 GP2AP007A00F	 GP2AP008T00F
 GP2AP030A00F	 GP2AP052A00F	 GP2AP052A00F	 GP2L26K2	 GP2M002A060FG
 GP2M004A060PG	 GP2M004A065FG	 GP2M004A065PG	 GP2M005A050PG	 GP2M005A060CG
 GP2M005A060FG	 GP2M005A060PGH	 GP2M008A060FGH	 GP2M010A060F	 GP2M010A065F
 GP2M012A080NG	 GP2M020A050H	 GP2M020A060N	 GP2S24J0000F	 GP2S27T3
 GP2S27T3J00F	 GP2S27V6	 GP2S29SVJ00F	 GP2S40JJ000F	 GP2S700HCP
 GP2S700HCP	 GP2W0004YP	 GP2W0110YPS	 GP2W0112YPOF	 GP2W0118YPS
 GP2W0150YP0F	 GP2W3104XP0F	 GP2W3104YP0F	 GP2W3106YP0F	 GP2W3152YP0F
 GP2W3172XP0F	 GP2W3270XP0F	 GP2Y0A02YK0F	 GP2Y0A02YK0F	 GP2Y0A21

Contact us: Info@Y-IC.com

HINZUFÜGEN: Einheit A5-B5 Nr.509, 5 / F Sing Win Fabrikgebäude, 15-17 Shing Yip St, Kwun Tong, Kowloon, HongKong.

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